

<b>L Number</b>	<b>Hits</b>	<b>Search Text</b>	<b>DB</b>	<b>Tim stamp</b>
-	165	((mon crystal or monocrystalline) near2 substrate) and (amorphous near oxide) and (metal near (oxide or nitride)) and ((cap or capping) adj layer) and (template adj layer) and oxide.clm. and oxide.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:41
-	150	((monocrystal or monocrystalline) near2 substrate) and (amorphous near oxide).clm. and (metal near (oxide or nitride)) and ((cap or capping) adj layer) and (template adj layer) and oxide.clm. and oxide.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:42
-	23	((monocrystal or monocrystalline) near2 substrate) and (amorphous near oxide).clm. and (metal near (oxide or nitride)) and ((cap or capping) adj layer).clm. and (template adj layer) and oxide.clm. and oxide.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:42
-	5	((monocrystal or monocrystalline) near2 substrate) and (amorphous near oxide).clm. and (metal near (oxide or nitride)).clm. and ((cap or capping) adj layer).clm. and (template adj layer) and oxide.clm. and oxide.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:42
-	23	((monocrystal or monocrystalline) near2 substrate) and (amorphous near oxide).clm. and (metal near (oxide or nitride)) and ((cap or capping) adj layer).clm. and (template adj layer) and oxide.clm. and oxide.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:49
-	12	((monocrystalline or monocrystal) near2 (substrate)) same (amorphous near2 oxide) same (metal near (oxide or nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:51
-	6	((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. same (metal near (oxide or nitride)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:52
-	20	((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and (metal near (oxide or nitride)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:53
-	194	((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:53
-	30	((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping) adj layer).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:53

-	30	((mon crystalline or monocrystal) near2 (substrate)).clm. and (amorph us n ar oxide).clm. and ((cap r apping) adj lay r).clm. and template	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:55
-	188	((m n crystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:55
-	34	((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:55
-	0	(((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping)).clm.) not (((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:55
-	154	(((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping))) not (((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping)).clm.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 16:55
-	4	(((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping)).clm.) not (((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping) adj layer).clm. and template)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 14:03
-	34	(((monocrystalline or monocrystal) near2 (substrate)).clm. and (amorphous near oxide).clm. and ((cap or capping)).clm.) and (template or (compound near semiconductor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 14:04